

Six-Pack NPT IGBT

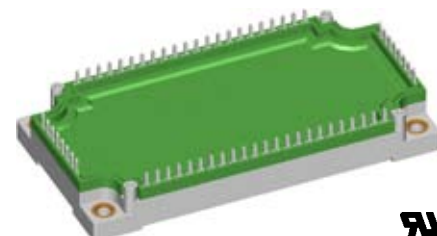
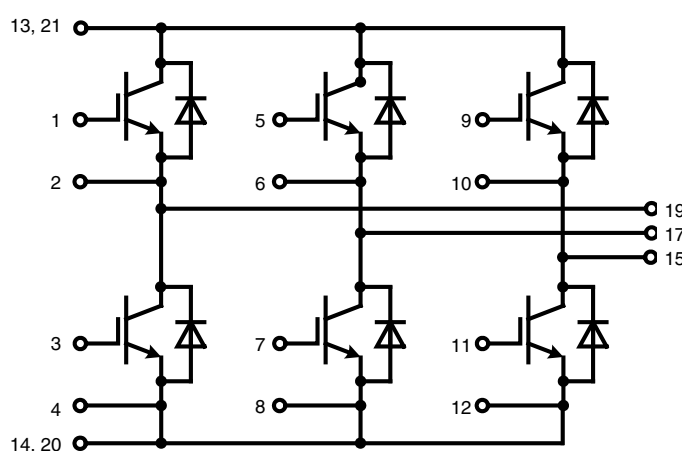
$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 125 \text{ A}$$

$$V_{CE(sat) \text{ typ.}} = 2.2 \text{ V}$$

Part name (Marking on product)

MWI 75-12A8




E 72873

Pin configuration see outlines.

Features:

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy parallelling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- space savings

Application:

- AC motor control
- AC servo and robot drives
- power supplies

Package:

- designed for wave soldering
- with copper base plate

Output Inverter T1 - T6

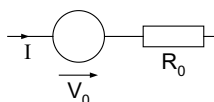
				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			125	A
I_{C80}		$T_C = 80^{\circ}\text{C}$			85	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			500	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75\text{ A}; V_{GE} = 15\text{ V}$		2.2 2.5	2.6	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 3\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	3	5	mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			400	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		5.5		nF
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 75\text{ A}$		350		nC
$t_{d(on)}$	turn-on delay time	} inductive load $V_{CE} = 600\text{ V}; I_C = 75\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 15\text{ }\Omega$	$T_{VJ} = 125^{\circ}\text{C}$	100		ns
t_r	current rise time			50		ns
$t_{d(off)}$	turn-off delay time			650		ns
t_f	current fall time			50		ns
E_{on}	turn-on energy per pulse			12.1		mJ
E_{off}	turn-off energy per pulse			10.5		mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 15\text{ }\Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} \leq 1200\text{ V}$		150	A
SCSOA	short circuit safe operating area					
t_{sc}	short circuit duration	$V_{CE} = 1200\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10	μs
I_{sc}	short circuit current	$R_G = 15\text{ }\Omega;$ non-repetitive		300		A
R_{thJC}	thermal resistance junction to case	(per IGBT)			0.25	K/W

Output Inverter D1 - D6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			150	A
I_{F80}		$T_C = 80^{\circ}\text{C}$			100	A
V_F	forward voltage	$I_F = 75\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.2 1.6	2.6	V V
I_{RM}	max. reverse recovery current	} $V_R = 600\text{ V}; I_F = 75\text{ A}; V_{GE} = 0\text{ V}$ $di_F/dt = -750\text{ A}/\mu\text{s}$	$T_{VJ} = 125^{\circ}\text{C}$	79		A
t_{rr}	reverse recovery time			220		ns
R_{thJC}	thermal resistance junction to case	(per diode)			0.41	K/W

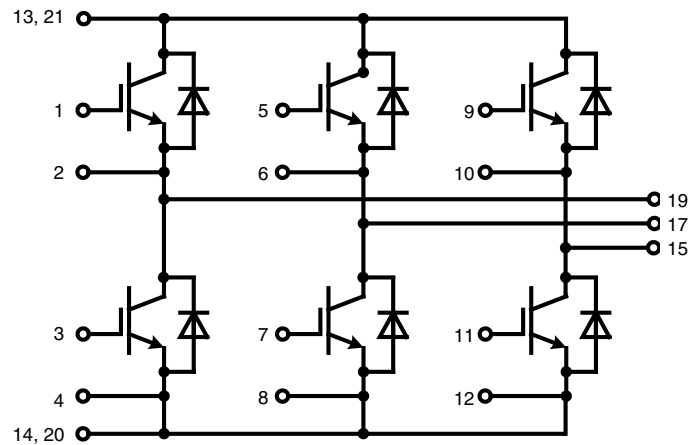
Module

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			2500	V~
M_d	mounting torque (M5)		3		6	Nm
d_s	creep distance on surface		10			mm
d_A	strike distance through air		10			mm
$R_{pin-chip}$	resistance pin to chip			1.8		mΩ
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.01		K/W
Weight				300		g

Equivalent Circuits for Simulation


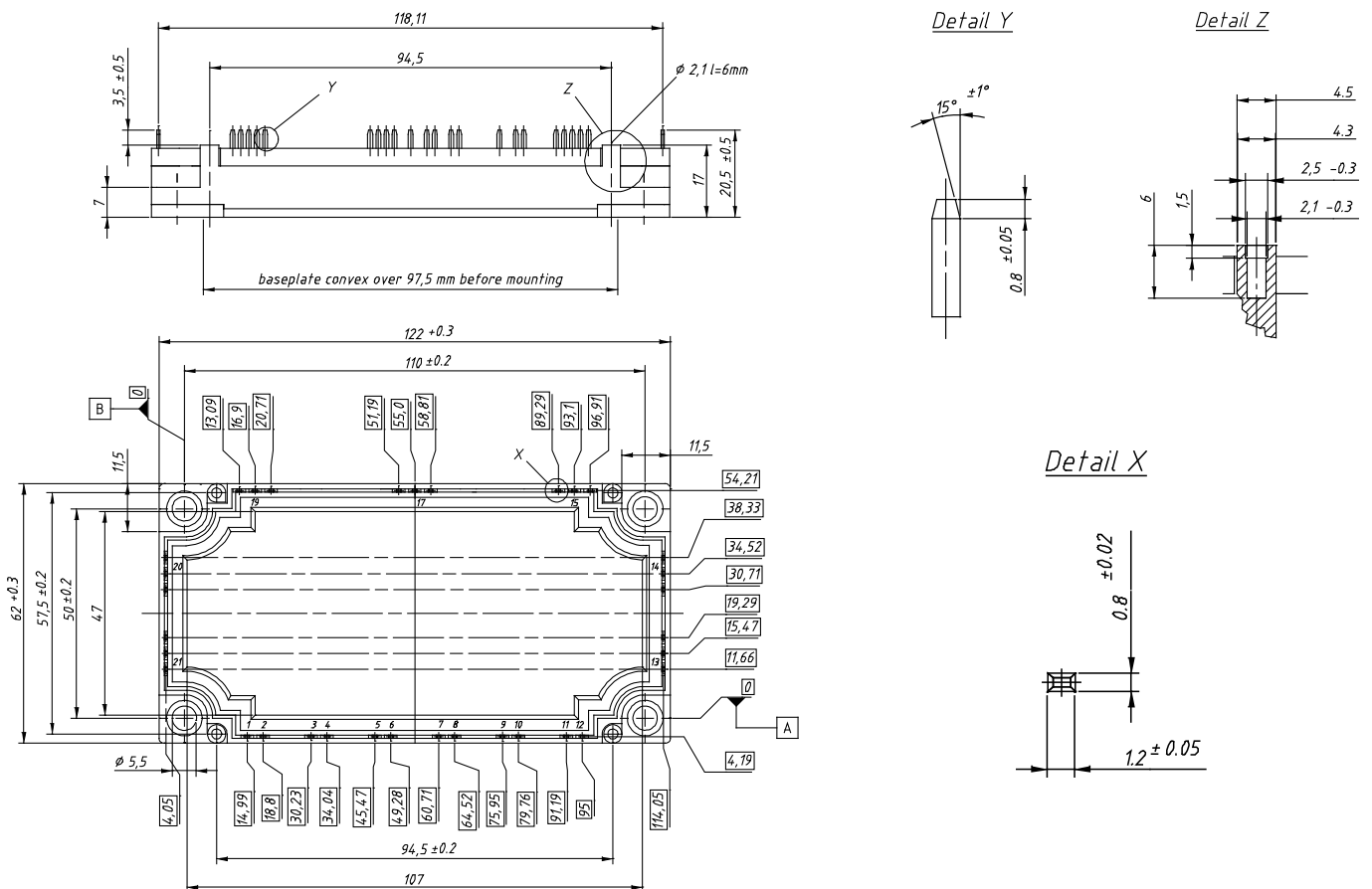
V ₀				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V ₀ R ₀	IGBT	T1 - T6 T _{VJ} = 125°C		1.5 13.5		V mΩ
V ₀ R ₀	Diode	D1 - D6 T _{VJ} = 125°C		1.3 4		V mΩ

Circuit Diagram



Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MWI75-12A8	MWI75-12A8	Box	5	486787

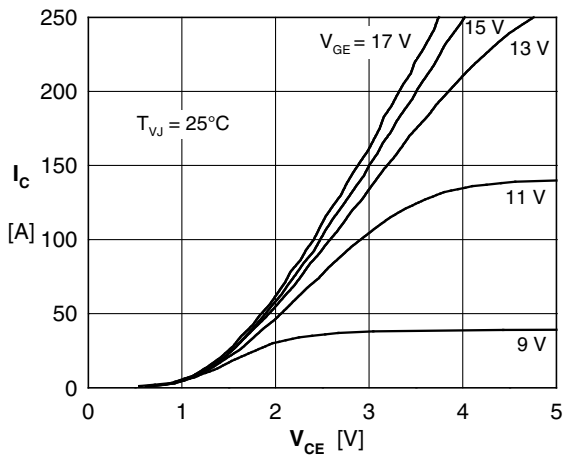


Fig. 1 Typ. output characteristics

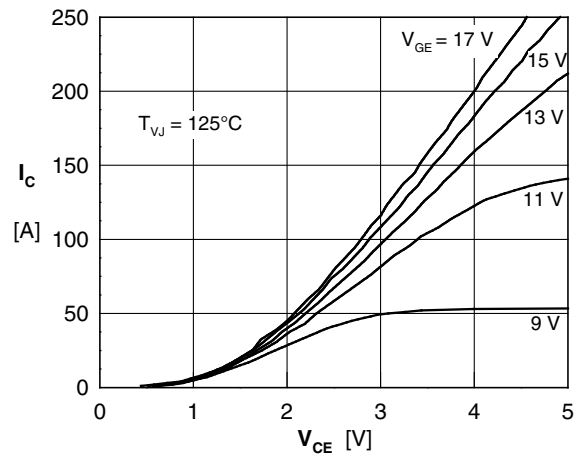


Fig. 2 Typ. output characteristics

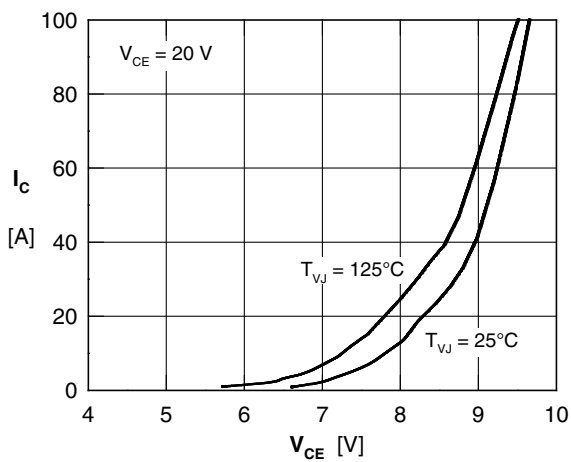


Fig. 3 Typ. transfer characteristics

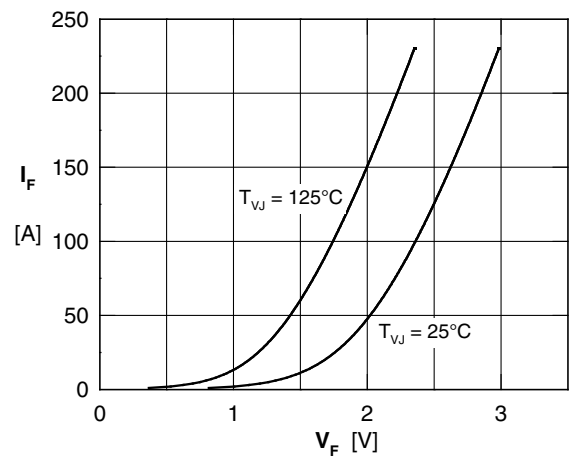


Fig. 4 Typ. forward characteristics of free wheeling diode

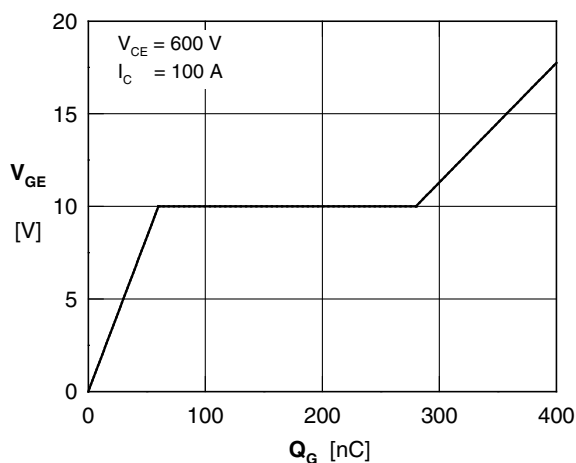


Fig. 5 Typ. turn on gate charge

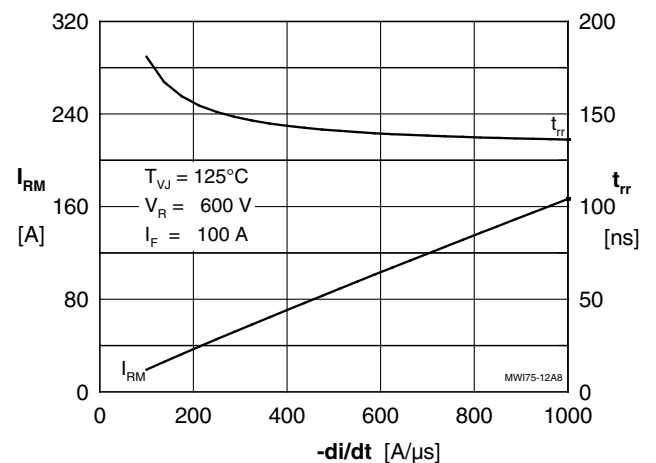


Fig. 6 Typ. turn off characteristics of free wheeling diode

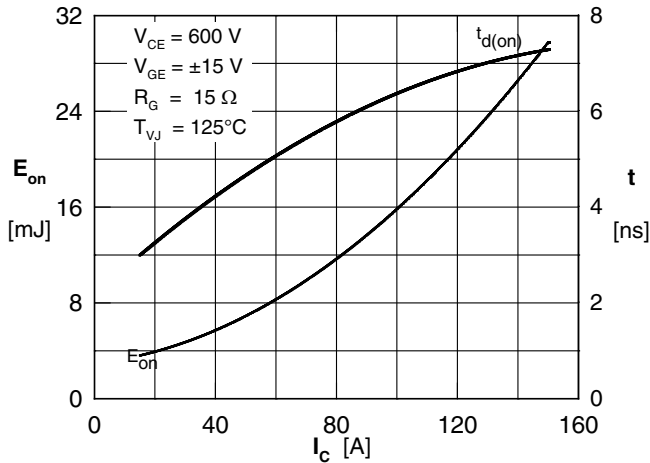


Fig. 7 Typ. turn on energy and switching times versus collector current

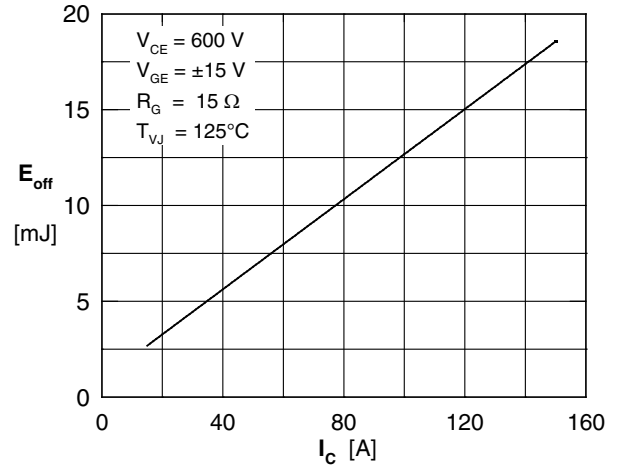


Fig. 8 Typ. turn off energy and switching times versus collector current

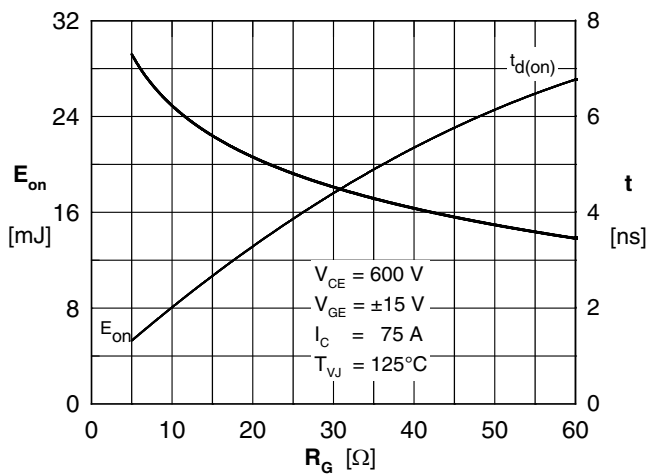


Fig. 9 Typ. turn on energy and switching times versus gate resistor

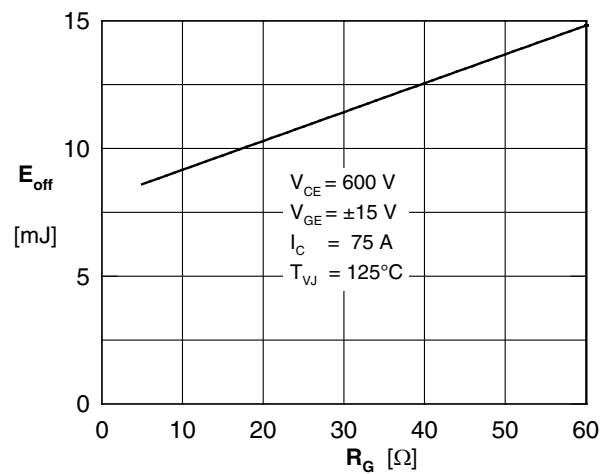


Fig. 10 Typ. turn off energy and switching times versus gate resistor

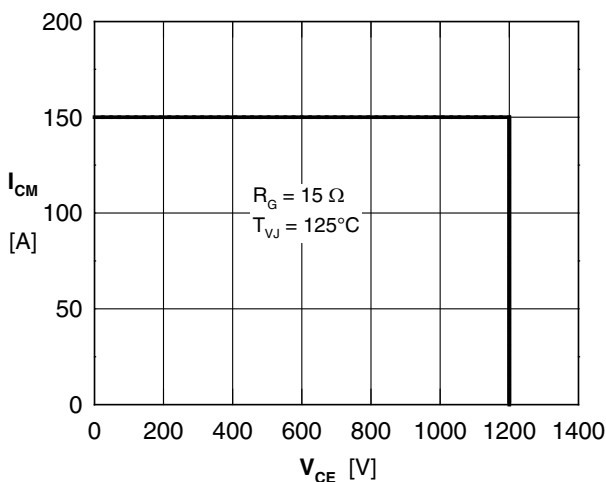


Fig. 11 Reverse biased safe operating area RBSOA

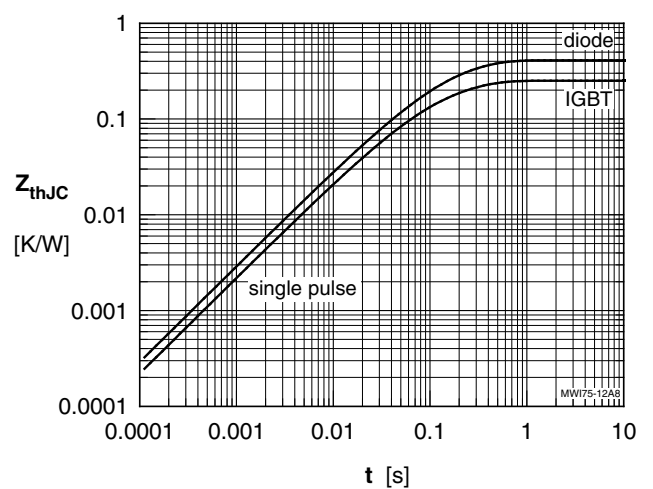


Fig. 12 Typ. transient thermal impedance